

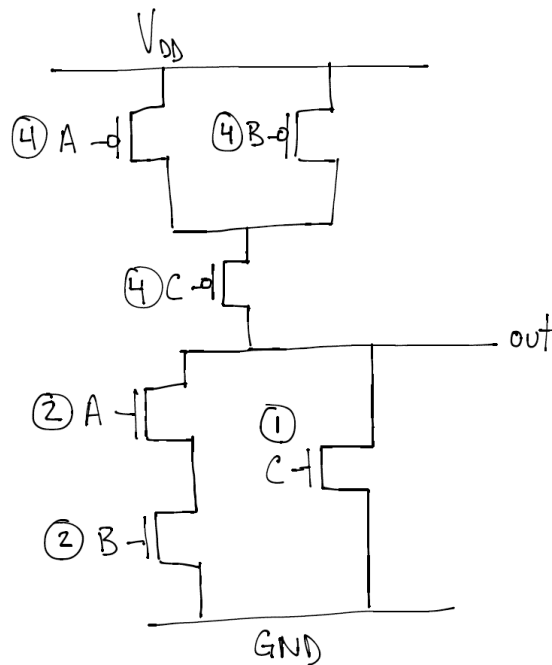
HW #3

(Lecture 4, 5 and 7)

Design a static complementary CMOS gate for logic function: $\overline{ab + c}$.

(1) Draw the transistor level schematic;

(2) Size the transistors so that each PDN and PUN has the same resistance as an inverter with 2:1 PMOS and NMOS size; **See sizing on drawing**



(3) Which input pattern gives the longest t_{phl}? How about t_{plh}?

[Format ABC]

Longest t_{phl}: 110

Longest t_{plh}: 100

(4) Assume that the external load capacitance is 1pF, the diffusion capacitance of a unit size PMOS/NMOS is 0.2pF. The equivalent resistance of NMOS and PMOS with L/W=1 are 15K Ω and 30K Ω respectively. Estimate the worst case t_{phl} and t_{plh} using Elmore model.

$$\text{Longest t}_{phl} = R_{cp} * C_p + R_{bn} * C_n + (R_{an} + R_{bn}) * C_l$$

$$= (30/4) * 0.2 + (15/2) * 0.2 + (15/2 + 15/2) * 1 = 7.5 * 0.2 + 7.5 * 0.2 + 15 * 1 = \mathbf{18\mu s}$$

$$\text{Longest t}_{plh} = R_{bp} * C_p + (R_{bp} + R_{cp}) * C_l + (R_{an} + R_{cn}) * C_n$$

$$= (30/4) * 0.2 + (30/4 + 30/4) * 1 + (15/2 + 15) * 0.2 = 7.5 * 0.2 + 15 * 1 + 22.5 * 0.2 = \mathbf{21\mu s}$$